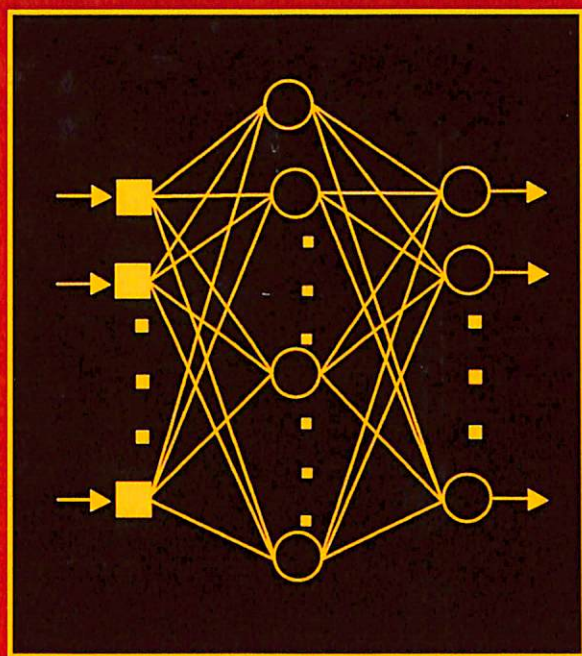


*Advances in*  
**COMPUTERS**

*Volume* **118**

*Durable Phase-Change Memory Architectures*



*Edited by*

**AN ASADINIA AND HAMID SARBASI-AZAD**

for  
**SON**



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